

# IRG4IBC20WPbF

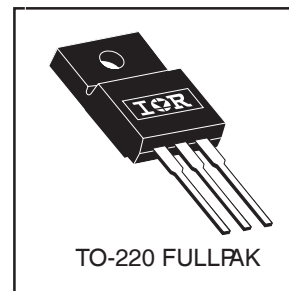
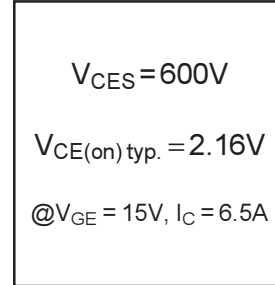
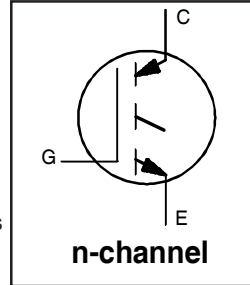
## INSULATED GATE BIPOLAR TRANSISTOR

### Features

- Designed expressly for Switch-Mode Power Supply and PFC (power factor correction) applications
- 2.5kV, 60s insulation voltage ©
- Industry-benchmark switching losses improve efficiency of all power supply topologies
- 50% reduction of Eoff parameter
- Low IGBT conduction losses
- Latest-generation IGBT design and construction offers tighter parameters distribution, exceptional reliability
- Industry standard Isolated TO-220 Fullpak™ outline
- Lead-Free

### Benefits

- Lower switching losses allow more cost-effective operation than power MOSFETs up to 150 kHz ("hard switched" mode)
- Of particular benefit to single-ended converters and boost PFC topologies 150W and higher
- Low conduction losses and minimal minority-carrier recombination make these an excellent option for resonant mode switching as well (up to >>300 kHz)



### Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Breakdown Voltage	600	V
$I_C @ T_C = 25^\circ\text{C}$	Continuous Collector Current	12	A
$I_C @ T_C = 100^\circ\text{C}$	Continuous Collector Current	6.0	
$I_{CM}$	Pulsed Collector Current ①	52	
$I_{LM}$	Clamped Inductive Load Current ②	52	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$E_{ARV}$	Reverse Voltage Avalanche Energy ③	200	mJ
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	34	W
$P_D @ T_C = 100^\circ\text{C}$	Maximum Power Dissipation	14	
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm) from case )	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

### Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	3.7	°C/W
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	65	
Wt	Weight	2.0 (0.07)	—	g (oz)

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

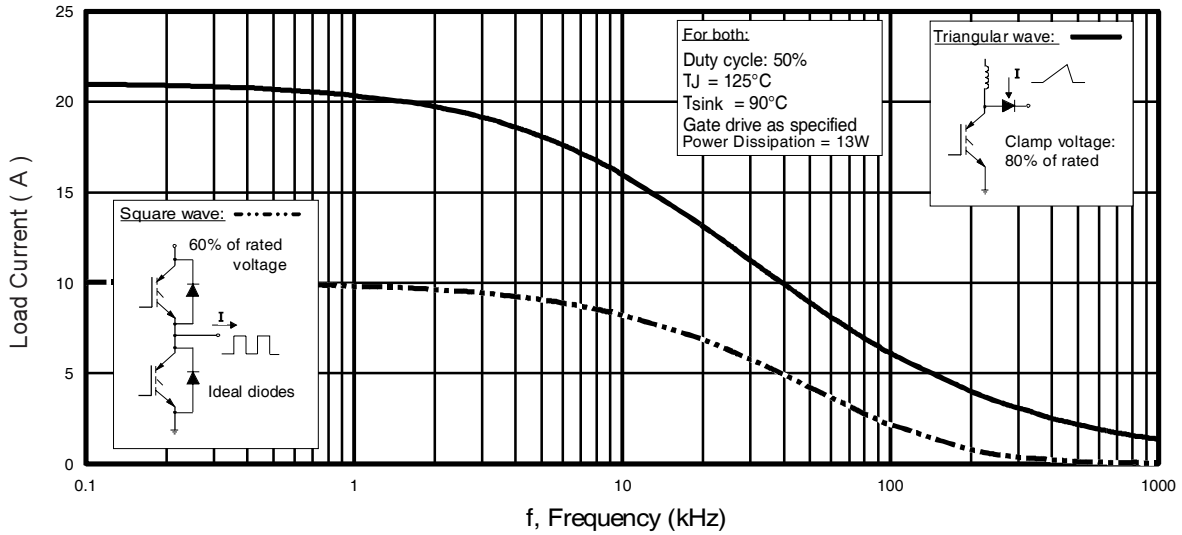
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.48	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	2.16	2.6	V	$I_C = 6.5A$ $V_{GE} = 15V$
		—	2.55	—		$I_C = 13A$ See Fig.2, 5
		—	2.05	—		$I_C = 6.5A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-8.8	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
$g_{fe}$	Forward Transconductance ⑤	5.5	8.3	—	S	$V_{CE} = 100V, I_C = 6.5A$
$I_{CES}$	Zero Gate Voltage Collector Current	—	—	250	$\mu A$	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

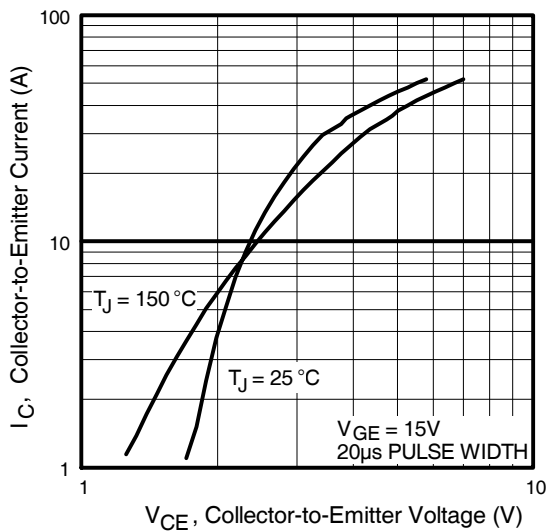
	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	—	26	38	nC	$I_C = 6.5A$
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	3.7	5.5		$V_{CC} = 400V$ See Fig.8
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	10	15		$V_{GE} = 15V$
$t_{d(on)}$	Turn-On Delay Time	—	22	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 6.5A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$
$t_r$	Rise Time	—	14	—		
$t_{d(off)}$	Turn-Off Delay Time	—	110	160		
$t_f$	Fall Time	—	64	96		
$E_{on}$	Turn-On Switching Loss	—	0.06	—	mJ	Energy losses include "tail" See Fig. 9, 10, 14
$E_{off}$	Turn-Off Switching Loss	—	0.08	—		
$E_{ts}$	Total Switching Loss	—	0.14	0.2	ns	$T_J = 150^\circ\text{C},$ $I_C = 6.5A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail" See Fig. 10, 11, 14
$t_{d(on)}$	Turn-On Delay Time	—	21	—		
$t_r$	Rise Time	—	15	—		
$t_{d(off)}$	Turn-Off Delay Time	—	150	—		
$t_f$	Fall Time	—	150	—	mJ	See Fig. 10, 11, 14
$E_{ts}$	Total Switching Loss	—	0.34	—		
$L_E$	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
$C_{ies}$	Input Capacitance	—	490	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ See Fig. 7 $f = 1.0MHz$
$C_{oes}$	Output Capacitance	—	38	—		
$C_{res}$	Reverse Transfer Capacitance	—	8.8	—		

### Notes:

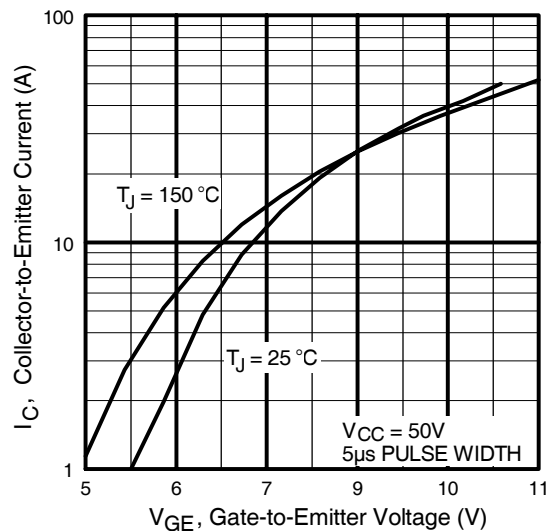
- ① Repetitive rating;  $V_{GE} = 20V$ , pulse width limited by max. junction temperature. ( See fig. 13b )
- ②  $V_{CC} = 80\%(V_{CES}), V_{GE} = 20V, L = 10\mu H, R_G = 50\Omega,$  (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ⑤ Pulse width  $5.0\mu s$ , single shot.
- ⑥  $t = 60s, f = 60Hz$



**Fig. 1 - Typical Load Current vs. Frequency**  
(Load Current =  $I_{RMS}$  of fundamental)

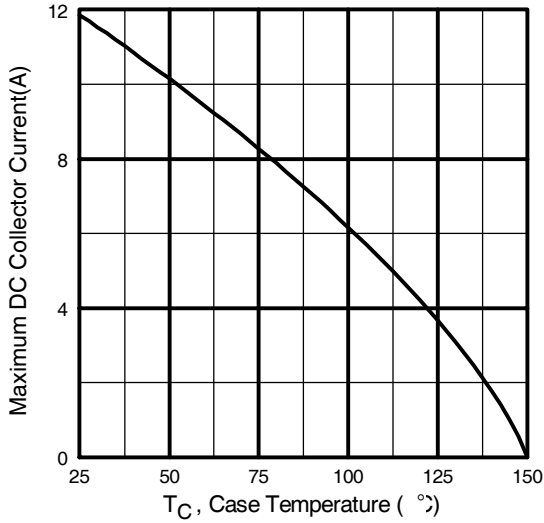


**Fig. 2 - Typical Output Characteristics**

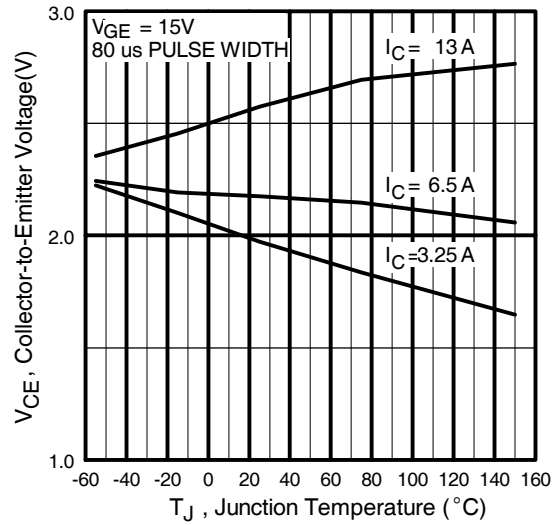


**Fig. 3 - Typical Transfer Characteristics**

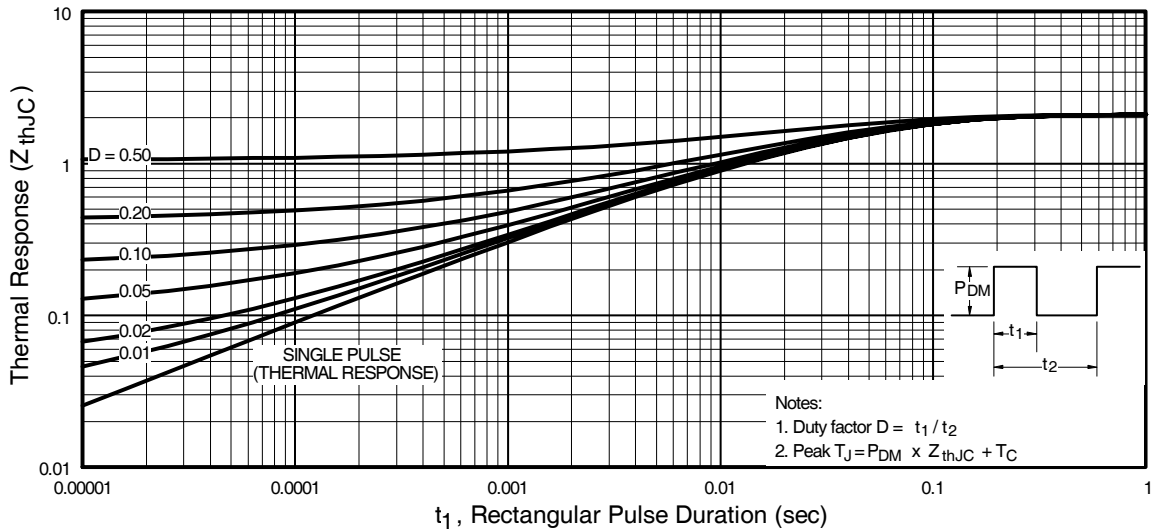
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**Fig. 4 - Maximum Collector Current vs. Case Temperature**

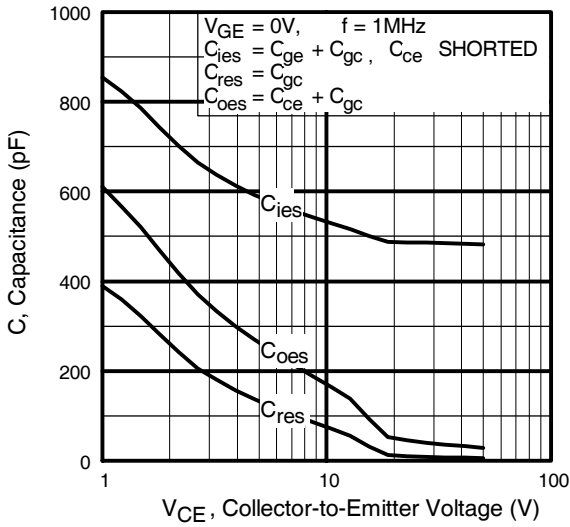


**Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature**

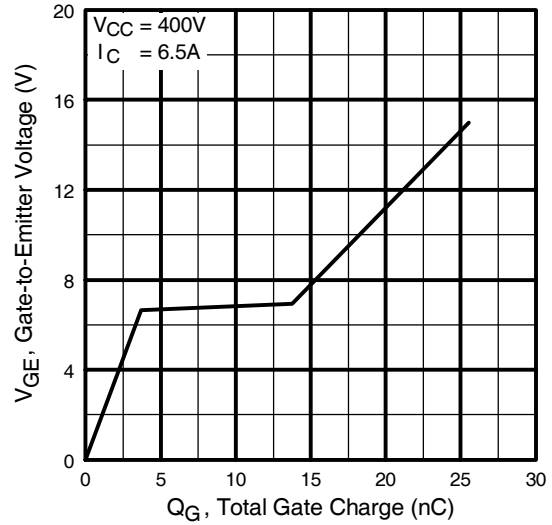


**Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**

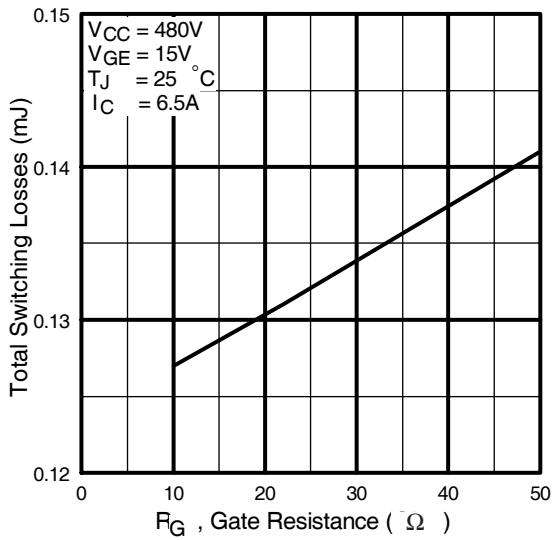
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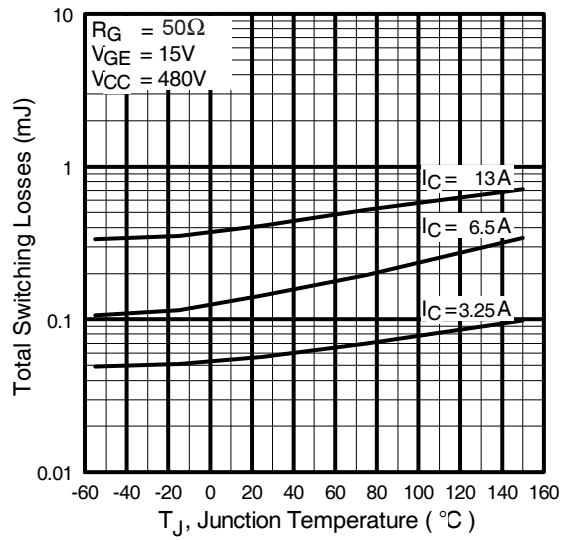
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage



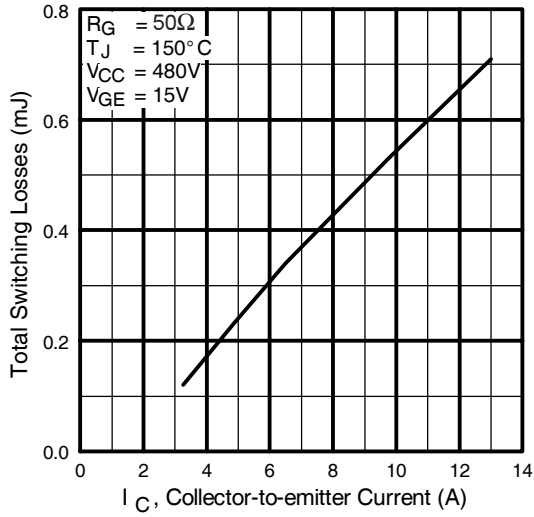
**Fig. 9** - Typical Switching Losses vs. Gate Resistance



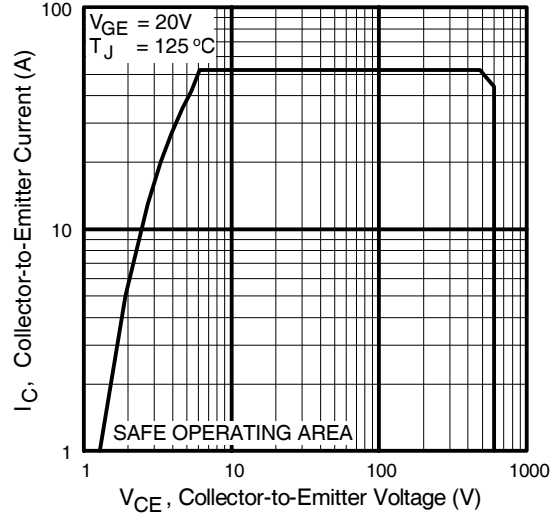
**Fig. 10** - Typical Switching Losses vs. Junction Temperature

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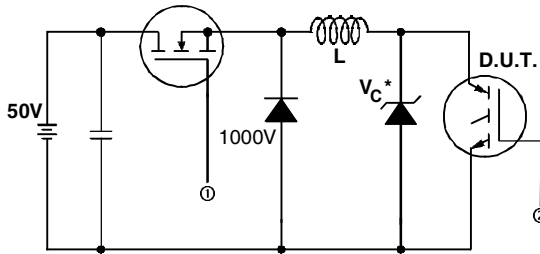
International  
**IR** Rectifier



**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current

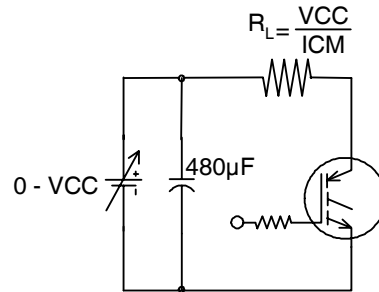


**Fig. 12** - Turn-Off SOA

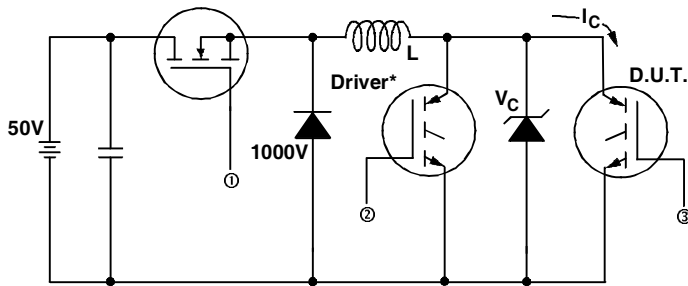


\* Driver same type as D.U.T.;  $V_c = 80\%$  of  $V_{ce(max)}$   
 \* Note: Due to the 50V power supply, pulse width and inductor will increase to obtain rated  $I_d$ .

**Fig. 13a** - Clamped Inductive Load Test Circuit

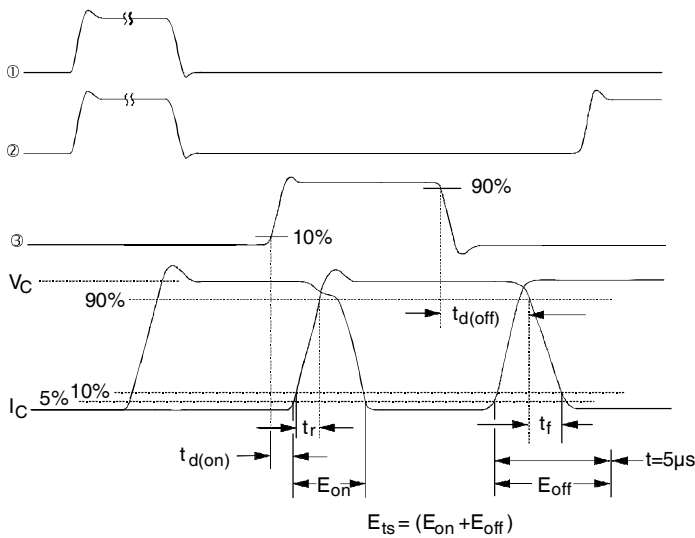


**Fig. 13b** - Pulsed Collector Current Test Circuit



**Fig. 14a** - Switching Loss Test Circuit

\* Driver same type as D.U.T.,  $V_C = 480V$



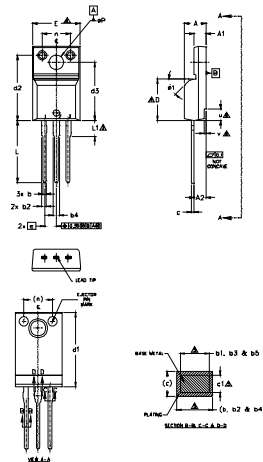
**Fig. 14b** - Switching Loss Waveforms

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## TO-220AB Full-Pak Package Outline

Dimensions are shown in millimeters (inches)



S Y M B O L	DIMENSIONS				N O T E S
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.57	4.83	.180	.190	
A1	2.57	2.85	.101	.111	
A2	2.51	2.93	.099	.115	
b	0.61	0.94	.024	.037	
b1	0.61	0.89	.024	.035	5
b2	0.76	1.27	.030	.050	
b3	0.76	1.22	.030	.048	5
b4	1.02	1.52	.040	.060	
b5	1.02	1.47	.040	.058	5
c	0.33	0.65	.015	.026	
c1	0.33	0.58	.013	.023	5
D	8.66	9.80	.341	.386	4
d1	15.80	16.15	.622	.635	
d2	13.97	14.22	.550	.560	
d3	12.30	12.93	.484	.509	
E	9.63	10.76	.379	.423	4
e	2.54	BSC	100	BSC	
L	13.20	13.72	.520	.540	
L1	3.37	3.67	.122	.145	3
n	6.05	6.60	.238	.260	
#P	3.05	3.45	.120	.136	
u	2.40	2.50	.094	.098	6
y	0.40	0.50	.016	.020	6
#Y	-	45°	-	45°	

NOTES:  
 1- DIMENSIONS AND TOLERANCING AS PER ASME Y14.5 M - 1994  
 2- DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES)  
 3- LEAD DIMENSION AND PITCH UNCONTROLLED IN U.S.  
 4- DIMENSION D & E DO NOT INCLUDE WELD FLASH; WELD FLASH SHALL NOT EXCEED .200 (0.079) PER SIDE; THESE DIMENSIONS ARE MEASURED AT THE OUTER MOST EXTREMES OF THE PLASTIC BODY.  
 5- DIMENSION AT A, B, B1 & C1 APPLY TO BASE METAL ONLY.  
 6- STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS 2 & 3 TO CONTROLLING DIMENSION 1 NOTES.

**LEAD ASSIGNMENTS**

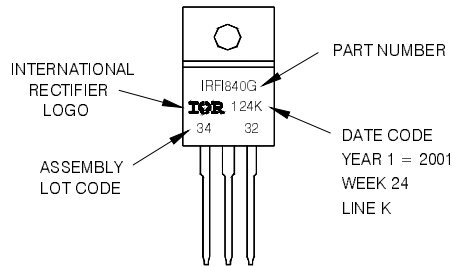
- 1- GATE
- 2- DIODE
- 3- SOURCE

- WELD GRAB**
- 1- GATE
  - 2- COLLECTOR
  - 3- EMITTER

## TO-220AB Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRFI840G  
 WITH ASSEMBLY  
 LOT CODE 3432  
 ASSEMBLED ON WW 24, 2001  
 IN THE ASSEMBLY LINE 'K'

Note: 'P' in assembly line position indicates 'Lead-Free'



TO-220AB Full-Pak package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.



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[RJH60D2DPP-M0#T2](#) [IKP20N60TXKSA1](#) [IHW20N65R5XKSA1](#) [APT70GR120JD60](#) [AOD5B60D](#) [APT70GR120L](#) [STGWT60H65FB](#)  
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